



NTD20N06T4G Information



For Reference Only

Part Number NTD20N06T4G
Manufacturer ON Semiconductor

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 60V 20A DPAK

Package TO-252-3, DPak (2 Leads + Tab), SC-63

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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NTD20N06T4G Specifications

Manufacturer Part Number NTD20N06T4G Manufacturer ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 20A (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 30nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1015pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.88W (Ta), 60W (Tj) Rds On (Max) @ Id, Vgs 46 mOhm @ 10A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package DPAK Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63 Report errors?		
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Series - N-Channel FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 20A (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 30nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1015pF @ 25V Vgs (Max) ±20V FET Feature Power Dissipation (Max) 1.88W (Ta), 60W (Tj) Rds On (Max) @ Id, Vgs 46 mOhm @ 10A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package DPAK Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C20A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs30nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1015pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.88W (Ta), 60W (Tj)Rds On (Max) @ Id, Vgs46 mOhm @ 10A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageDPAKPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Package	TO-252-3, DPak (2 Leads + Tab), SC-63
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C20A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs30nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1015pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.88W (Ta), 60W (Tj)Rds On (Max) @ Id, Vgs46 mOhm @ 10A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageDPAKPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Series	-
Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C20A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs30nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1015pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.88W (Ta), 60W (Tj)Rds On (Max) @ Id, Vgs46 mOhm @ 10A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageDPAKPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 46 mOhm @ 10A, 10V Operating Temperature Supplier Device Package Package / Case 20A (Ta) 4V @ 250μA 30nC @ 10V 1015pF @ 25V 420V FET Feature - Power Dissipation (Max) 1.88W (Ta), 60W (Tj) 46 mOhm @ 10A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount DPAK TO-252-3, DPak (2 Leads + Tab), SC-63	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs30nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1015pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)1.88W (Ta), 60W (Tj)Rds On (Max) @ Id, Vgs46 mOhm @ 10A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageDPAKPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package DPAK Package / Case 40 W (250μA 40 IOV 1.00 E 10V 1.015pF @ 25V 25V 26V 27V 27V 28V 28V 29V 1.88W (Ta), 60W (Tj) 46 mOhm @ 10A, 10V 29V 20F 20F 20F 20F 20F 20F 20F 20	Current - Continuous Drain (Id) @ 25°C	20A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 46 mOhm @ 10A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package DPAK Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 1015pF @ 25V Vgs (Max) E20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 46 mOhm @ 10A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package DPAK Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max) ± 20 VFET Feature-Power Dissipation (Max) 1.88 W (Ta), 60 W (Tj)Rds On (Max) @ Id, Vgs 46 mOhm @ 10 A, 10 VOperating Temperature -55° C $\sim 175^{\circ}$ C (TJ)Mounting TypeSurface MountSupplier Device PackageDPAKPackage / CaseTO- 252 -3, DPak (2 Leads + Tab), SC- 63	Gate Charge (Qg) (Max) @ Vgs	30nC @ 10V
FET Feature - Power Dissipation (Max) 1.88W (Ta), 60W (Tj) Rds On (Max) @ Id, Vgs 46 mOhm @ 10A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package DPAK Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Input Capacitance (Ciss) (Max) @ Vds	1015pF @ 25V
Power Dissipation (Max) 1.88W (Ta), 60W (Tj) 46 mOhm @ 10A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package DPAK Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs46 mOhm @ 10A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackageDPAKPackage / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package DPAK Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Power Dissipation (Max)	1.88W (Ta), 60W (Tj)
Mounting Type Surface Mount Supplier Device Package DPAK Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Rds On (Max) @ Id, Vgs	46 mOhm @ 10A, 10V
Supplier Device Package DPAK Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Mounting Type	Surface Mount
	Supplier Device Package	DPAK
Report errors?	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63
		Report errors?

NTD20N06T4G Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

NTD20N06T4G Payment Methods





















NTD20N06T4G Shipping Methods













If you have any question about NTD20N06T4G, please do not hesitate to contact us!

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